

2011年 発表文献リスト

(論文発表)

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2. Md. T. Hasan, H. Tokuda, and M. Kuzuhara, "Surface barrier height lowering at above 540 K in AlInN/AlN/GaN heterostructures," *Appl. Phys. Lett.* vol. 99, 132102, Sept. (2011).

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2. K. Kodama, H. Tokuda, and M. Kuzuhara, "Theoretical calculation of impact ionization coefficients considering band index for wurzite Ga<sub>N</sub>," *9<sup>th</sup> Topical Workshop on Heterostructure Microelectronics*, Aug. pp. 105-106 (2011).
3. M. Hatano, J. Yamazaki, N. Yafune, S. Hashimoto, K. Akita, Y. Yamamoto, and M. Kuzuhara, "High-temperature RF characterization of AlGa<sub>N</sub>-channel HEMTs," *9<sup>th</sup> Topical Workshop on Heterostructure Microelectronics*, Aug. (2011).
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7. T. Saito, K. Nitanda, A. Syahiman, H. Tokuda, and M. Kuzuhara, "Temperature-dependent reverse leakage current characterization of n-Ga<sub>N</sub> Schottky diodes," *Intl. Meeting for Future of Electron Devices*, May (2011).
8. M. Kuzuhara and H. Tokuda, "Nitride-based heterojunction transistors for low-loss and high-power electronics," *EDIS 2011*. (Invited)
9. M. Kuzuhara, "Next challenges in III-Nitride HEMTs," *Workshop on Frontier Photonic and Electronic Materials and Devices*, March, 2011. (Invited)